

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (line edge curve points) WITH ((outside outer) AND (inner inside))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:06
L2	1	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (line edge curve points) WITH ((first outside outer) AND (second inner inside))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:07
L3	1	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (first outside outer) AND (second inner inside)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:08
L4	1	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (first outside outer) AND (second inner inside)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:08
L5	5	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance) WITH (curve curvature) AND (first outside outer) AND (second inner inside)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:09
L6	6	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance) WITH (curve curvature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:11
L7	6	(348/136.ccls. 348/129-130.ccls.) AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance) WITH (curve curvature nonlinear)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:11
L8	6826	("348" "382" "250").clas. AND (mask	US-PGPUB;	OR	ON	2011/10/06

		photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear)	USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB			14:12
L9	1606	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH (inner outer second two)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:12
L10	61	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH (inner outer second two) WITH edge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:13
L11	273	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH edge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:39
L12	63	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH edge AND rough\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:40
L13	22	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH edge AND rough\$3 NOT roughly	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:41
L14	42	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH edge AND (methodology rough\$3) NOT roughly	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:42
L15	21	("348" "382" "250").clas. AND (mask photomask circuit semiconductor wafer reticle) AND (match\$3 difference variance correlat\$3) WITH (curve curvature nonlinear) WITH edge AND (roughness ridges) NOT roughly	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/06 14:48
S1	5	US-6839470-\$.DID. OR US-1257940-\$.DID. OR JP-19990924-\$.DID. OR US-1287630-\$.DID. OR JP-19991019-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/12 16:01
S2	5	US-6839470-\$.DID. OR US-1257940-\$.DID. OR JP-19990924-\$.DID. OR US-	US-PGPUB; USPAT;	OR	ON	2011/04/12 16:02

		1287630-\$.DID. OR JP-19991019-\$.DID.	USOCR; JPO			
S3	6	US-6839470-\$.DID. OR US-1257940-\$.DID. OR JP-19990924-\$.DID. OR US-1287630-\$.DID. OR JP-19991019-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/12 16:02
S4	46766	US-6839470-\$.DID. OR US-1257940-\$.DID. OR "19990924" OR US-1287630-\$.DID. OR "19991019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/12 16:03
S5	46760	"19990924" OR "19991019"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/12 16:03
S6	38280	"19990924" OR "19991019" AND JP	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/04/12 16:03
S7	12582	"19990924" OR "19991019" AND JP	JPO	OR	ON	2011/04/12 16:04
S8	0	"JP-19990924" OR "JP-19991019"	JPO	OR	ON	2011/04/12 16:04
S9	0	"JP19990924" OR "JP19991019"	JPO	OR	ON	2011/04/12 16:04
S10	0	(JP near4 "19990924") OR (JP near3 JP19991019)	JPO	OR	ON	2011/04/12 16:05
S11	0	"200331469"	US-PGPUB; USPAT; JPO	OR	ON	2011/04/12 16:06
S12	2	"2003-31469"	US-PGPUB; USPAT; JPO	OR	ON	2011/04/12 16:06
S13	6	"2003-31469" 11-257940 11-287630	US-PGPUB; USPAT; JPO	OR	ON	2011/04/12 16:06
S14	9	"1279923"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO	OR	ON	2011/04/12 17:19
S15	1	"6480807".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO	OR	ON	2011/04/12 17:20
S16	1	"20090114816"	US-PGPUB; USPAT;	OR	ON	2011/04/13 14:06

			USOCR			
S17	0	hitachi.as. AND "1279923"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:37
S18	8	"1279923"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:37
S19	634	hitachi AND circuit WITH pattern WITH inspection	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:38
S20	221	hitachi AND circuit WITH pattern WITH inspection WITH system	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:39
S21	108	hitachi AND circuit WITH pattern WITH inspection WITH system AND failure	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:39
S22	40	hitachi AND circuit WITH pattern WITH inspection WITH system WITH failure	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:39
S23	8	hitachi AND circuit WITH pattern WITH inspection WITH system WITH failure WITH fabricating	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:39
S24	1	hitachi AND circuit WITH pattern WITH inspection WITH system WITH failure WITH fabricating WITH shape	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:40
S25	2	"20030021463"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/13 15:44
S26	42	contact NEAR2 edge NEAR2 roughness	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/14 09:26
S27	18	angle AND (contact NEAR2 edge NEAR2 roughness)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/14 09:27
S28	5651	angle SAME contact SAME edge SAME rough\$4	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/14 09:29
S29	4514	angle SAME contact SAME edge SAME rough\$4 AND (length distance)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/14 09:30
S30	164	angle SAME contact SAME edge SAME rough\$4 AND (length distance) AND (wafer (integrated ADJ circuit))	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/14 09:32
S31	1	"20030190069"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 14:36
S32	2	"20030021463"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 14:36
S33	13	"6839470"	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 14:39
S34	3212	tam.in. chase.in. AND (edge roughness)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 15:46
S35	2530	tam.in. chase.in. AND (edge roughness) AND (IC wafer substrate)	US-PGPUB; USPAT;	OR	ON	2011/04/16 15:47

			USOCR			
S36	2324	tam.in. chase.in. AND edge AND roughness AND (IC wafer substrate)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 15:47
S37	30	(tam.in. chase.in.) AND edge AND roughness AND (IC wafer substrate)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 15:48
S38	338	"382".clas. AND edge AND roughness AND (IC wafer substrate)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 15:51
S39	1344	("382".clas. "250".clas.) AND edge AND roughness AND (IC wafer substrate)	US-PGPUB; USPAT; USOCR	OR	ON	2011/04/16 15:54
S40	28	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH curve	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/04 10:57
S41	0	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH curve WITH (texture rough\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/04 14:15
S42	0	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH curve\$ WITH (texture rough\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/04 14:16
S43	2	"6480807".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/04 16:24
S44	2	"6480807".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/04 16:28
S45	0	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH curve\$ AND (texture rough\$4) AND (average WITH distance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 11:56
S46	2	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) SAME curve\$ AND (texture rough\$4) AND	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO;	OR	ON	2011/10/05 11:56

		(average WITH distance)	DERWENT; IBM_TDB			
S47	3	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) SAME curve\$ AND (texture rough\$4) AND (averag\$3 WITH distance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 11:57
S48	60	("382" "250").clas. AND template WITH (difference discrepancy variant variation variance divergency departure dissonance variableness variability) AND curve\$ AND (texture rough\$4) AND (averag\$3 WITH distance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 11:58
S49	232	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 WITH distance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:08
S50	4	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 WITH distance WITH square)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:21
S51	168	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 WITH distance) AND (mask photomask circuit semiconductor wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:28
S52	75	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 distance) AND (mask photomask circuit semiconductor wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:28
S53	75	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 distance) AND (mask photomask circuit semiconductor wafer reticle)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:35
S54	26	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 12:45
S55	5	("382" "250").clas. AND (difference discrepancy variant variation variance	US-PGPUB; USPAT;	OR	ON	2011/10/05 12:58

		divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB			
S56	2	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:02
S57	2	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability match\$3) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:12
S58	20	(difference discrepancy variant variation variance divergency departure dissonance variableness variability match\$3) WITH (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:29
S59	2	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability match\$3) SAME (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:30
S60	3	("382" "250").clas. AND (difference discrepancy variant variation variance divergency departure dissonance variableness variability match\$3) AND (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:30
S61	3	("382" "250").clas. AND (curve\$ curvature) AND (texture rough\$4) AND (averag\$3 NEAR2 square\$) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR2 freedom) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:31
S62	3	("382" "250").clas. AND (curve\$ curvature) AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR2 freedom) AND (averag\$3 WITH square\$ WITH	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO;	OR	ON	2011/10/05 13:35



		difference) AND fourier	DERWENT; IBM_TDB			
S63	8	("382" "250").clas. AND (curve\$ curvature) AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR2 freedom) AND (averag\$3 SAME square\$ SAME difference) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:36
S64	8	("382" "250").clas. AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (degree NEAR2 freedom) AND (averag\$3 SAME square\$ SAME difference) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:37
S65	10	("382" "250").clas. AND (texture rough\$4) AND (degree NEAR2 freedom) AND (averag\$3 SAME square\$ SAME difference) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:37
S66	163	("382" "250").clas. AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (averag\$3 SAME square\$ SAME difference) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:39
S67	26	("382" "250").clas. AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (averag\$3 WITH square\$ WITH difference) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:39
S68	22	("382" "250").clas. AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (averag\$3 WITH square\$ WITH difference) AND (curve curvature) AND fourier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 13:51
S69	9	("382" "250").clas. AND (texture rough\$4) AND (mask photomask circuit semiconductor wafer) AND (averag\$3 WITH square\$ WITH difference) AND (curve curvature) AND outer AND inner	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 15:55
S70	20	("382" "250").clas. AND (mask photomask circuit semiconductor wafer) AND (averag\$3 WITH square\$ WITH difference) AND (curve curvature) AND outer AND inner	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 16:00
S71	66	("382" "250").clas. AND (mask photomask circuit semiconductor wafer) AND (averag\$3 WITH square\$ WITH	US-PGPUB; USPAT; USOCR;	OR	ON	2011/10/05 16:01



		difference) AND (curve curvature) AND (outside outer) AND (inner inside)	FPRS; EPO; JPO; DERWENT; IBM_TDB			
S72	72	("382" "250").clas. AND (mask photomask circuit semiconductor wafer).ab. AND (match\$3 difference variance) NEAR2 (curve curvature) AND (outside outer) AND (inner inside)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 16:10
S73	11	("382" "250").clas. AND (mask photomask circuit semiconductor wafer).ab. AND (match\$3 difference variance) NEAR2 (curve curvature) AND (line edge curve) WITH ((outside outer) AND (inner inside))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 16:15
S74	87	("382" "250").clas. AND (mask photomask circuit semiconductor wafer) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (line edge curve) WITH ((outside outer) AND (inner inside))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 16:24
S75	103	("382" "250").clas. AND (mask photomask circuit semiconductor wafer) AND (match\$3 difference variance) NEAR2 (curve curvature) AND (line edge curve points) WITH ((outside outer) AND (inner inside))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/10/05 16:28

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